

P-Channel Enhancement Mode Power MOSFET

DESCRIPTION

The HM4P15Q uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V.

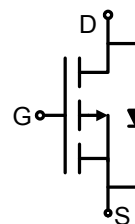
GENERAL FEATURES

- $V_{DS} = -150V, I_D = -4A$
 $R_{DS(ON)} < 980m\Omega @ V_{GS} = -6V$
 $R_{DS(ON)} < 780m\Omega @ V_{GS} = -10V$

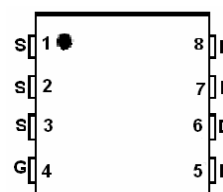
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- Battery Switch
- Load switch
- Power management



Schematic diagram



Marking and pin assignment

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM4P15Q	HM4P15Q	DFN3X3-8L	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-150	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-4	A
Drain Current-Pulsed (Note 1)	I_{DM}	-12	A
Maximum Power Dissipation	P_D	50	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	40	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-30	-33	-	V

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-150V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-2	-	-4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-1A	-	-	780	mΩ
		V _{GS} =-6.0V, I _D =-0.5A	-	-	980	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-15V,I _D =-9.1A	10	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-15V,V _{GS} =0V, F=1.0MHz	-	1600	-	PF
Output Capacitance	C _{oss}		-	350	-	PF
Reverse Transfer Capacitance	C _{rss}		-	300	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, ID=-1A, V _{GS} =-10V,R _{GEN} =6Ω	-	10	-	nS
Turn-on Rise Time	t _r		-	15	-	nS
Turn-Off Delay Time	t _{d(off)}		-	110	-	nS
Turn-Off Fall Time	t _f			70	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V,I _D =-9.1A V _{GS} =-10V	-	30	-	nC
Gate-Source Charge	Q _{gs}		-	5.5	-	nC
Gate-Drain Charge	Q _{gd}		-	8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-2.1A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

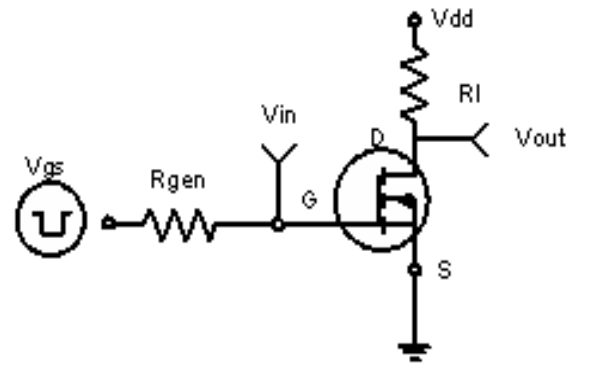


Figure 1:Switching Test Circuit

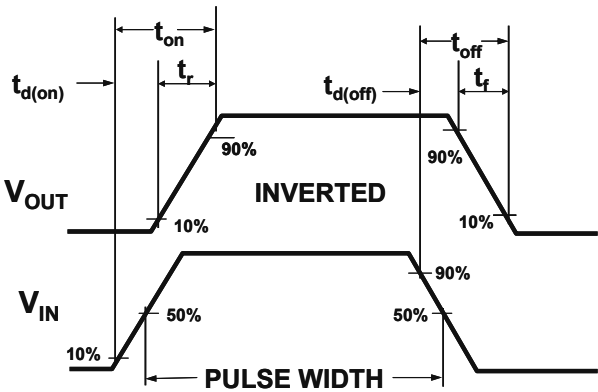


Figure 2:Switching Waveforms

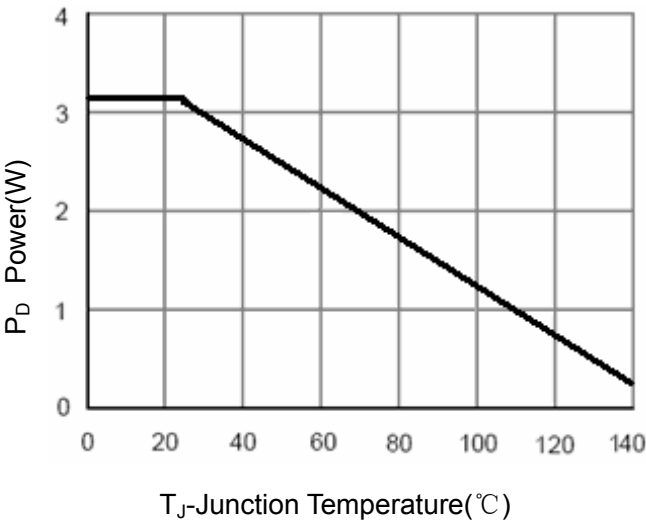


Figure 3 Power Dissipation

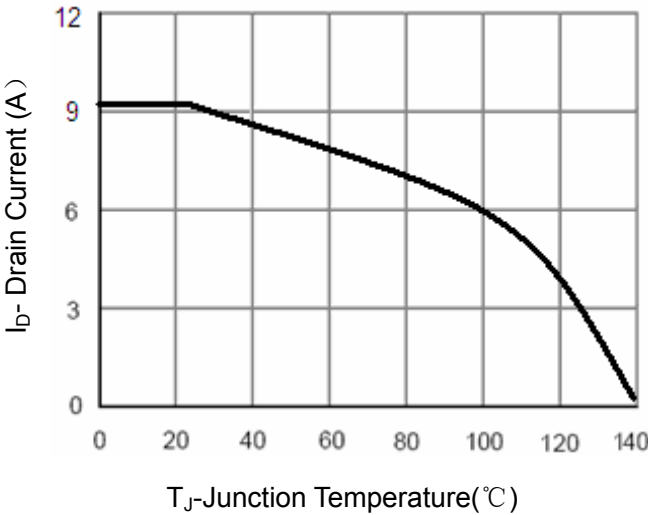


Figure 4 Drain Current

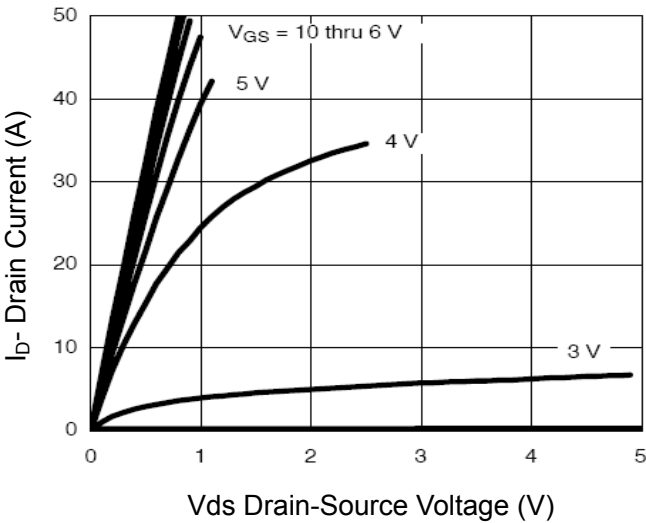


Figure 5 Output CHARACTERISTICS

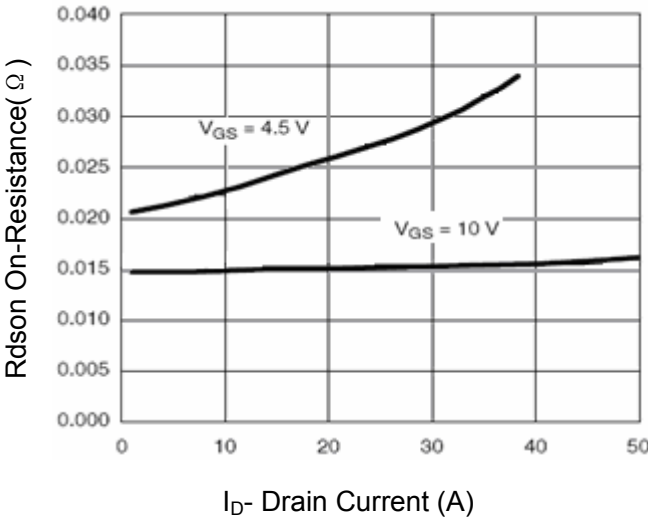


Figure 6 Drain-Source On-Resistance

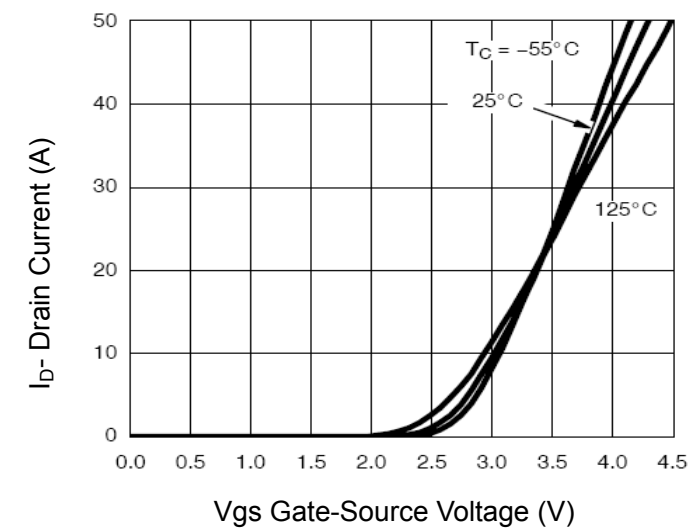


Figure 7 Transfer Characteristics

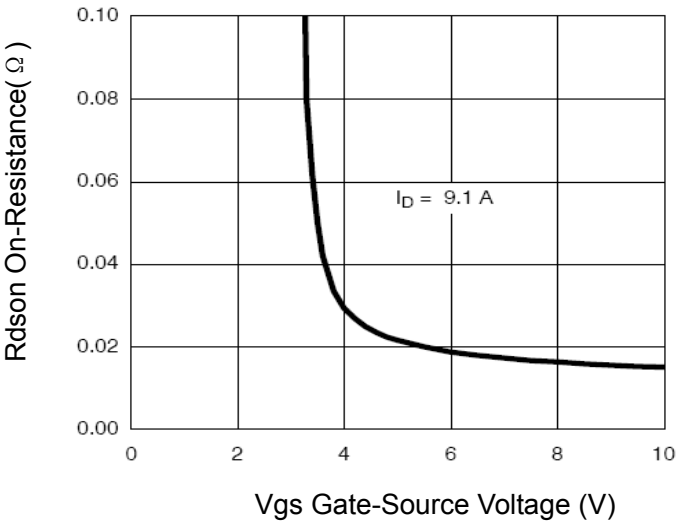


Figure 9 Rdson vs Vgs

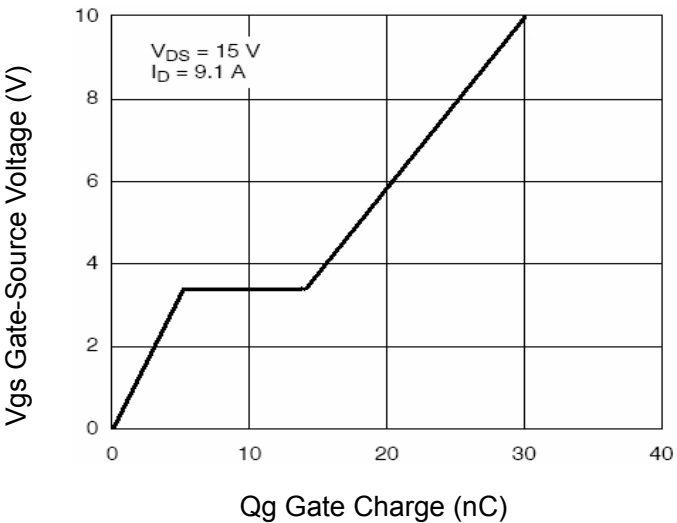


Figure 11 Gate Charge

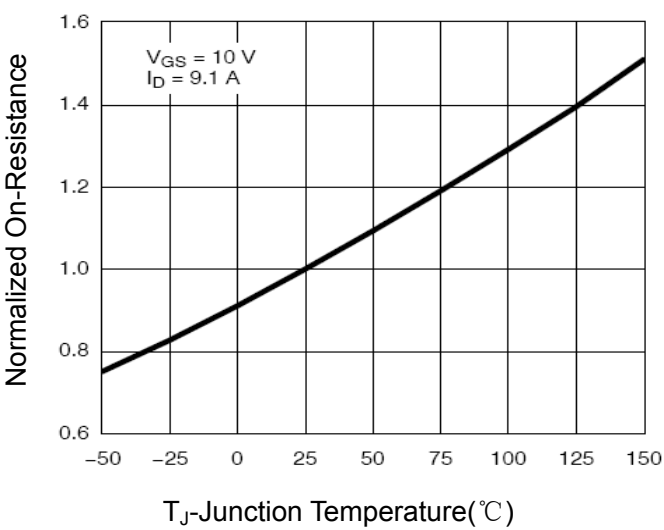


Figure 8 Drain-Source On-Resistance

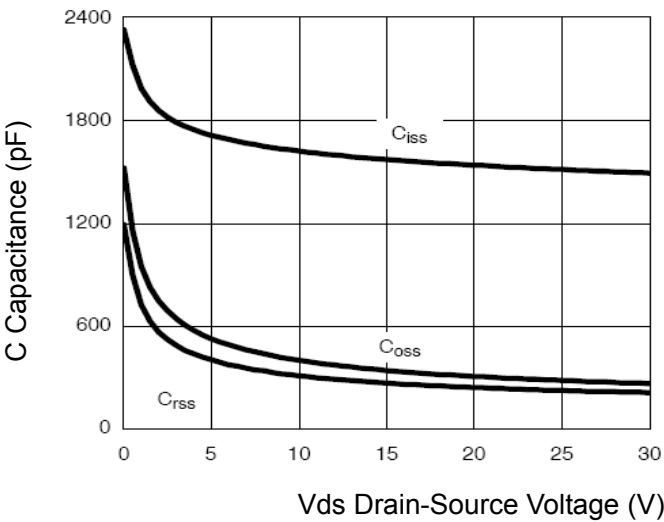


Figure 10 Capacitance vs Vds

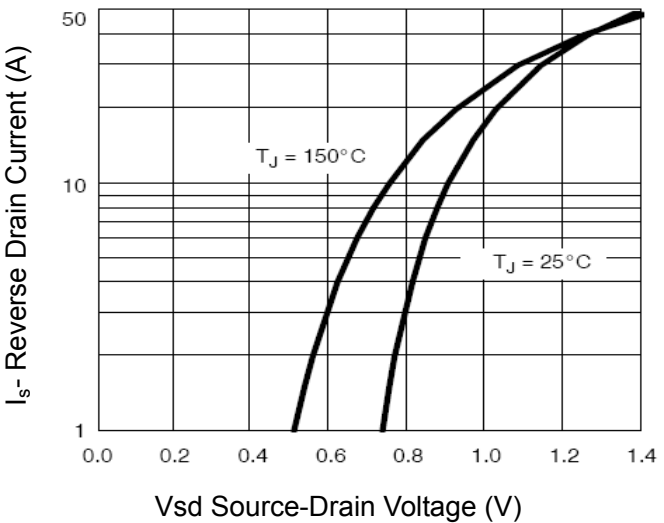


Figure 12 Source- Drain Diode Forward

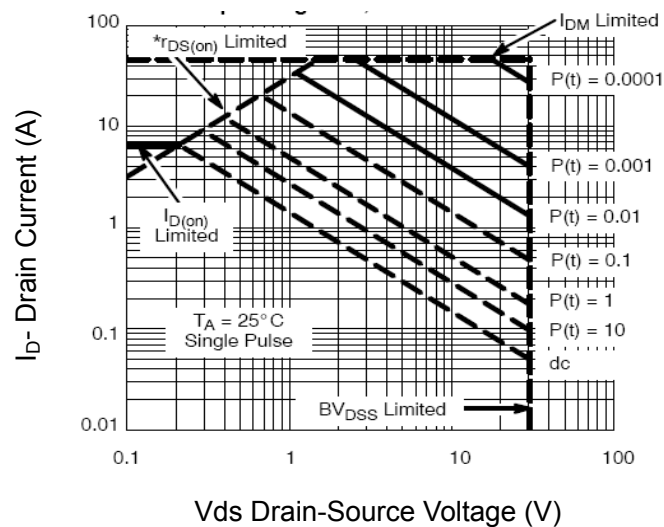


Figure 13 Safe Operation Area

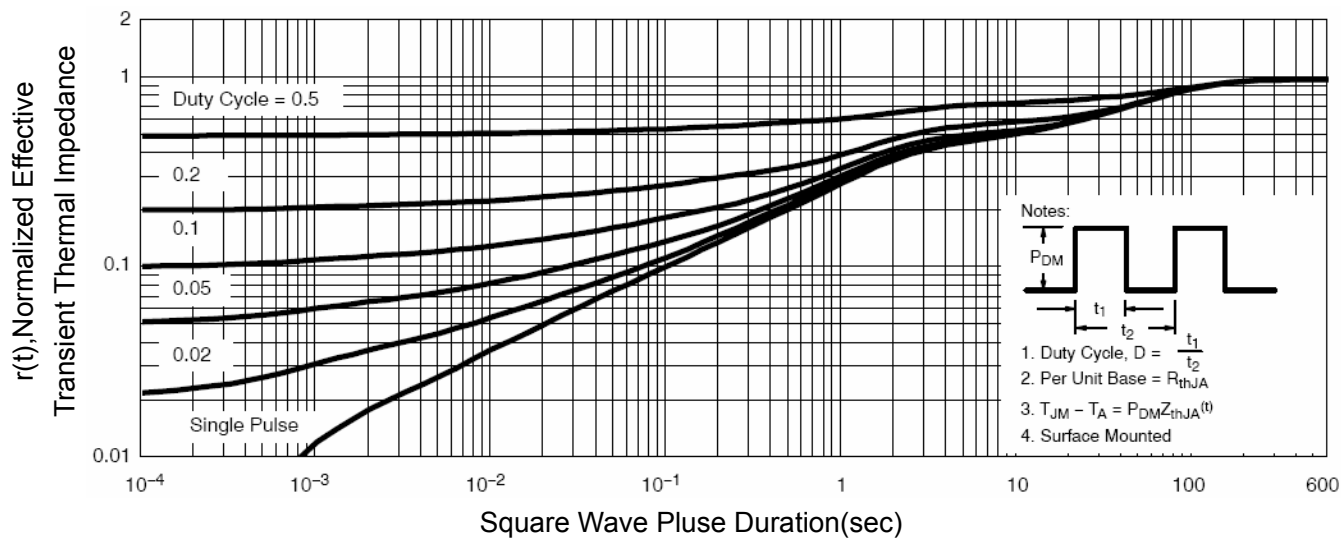
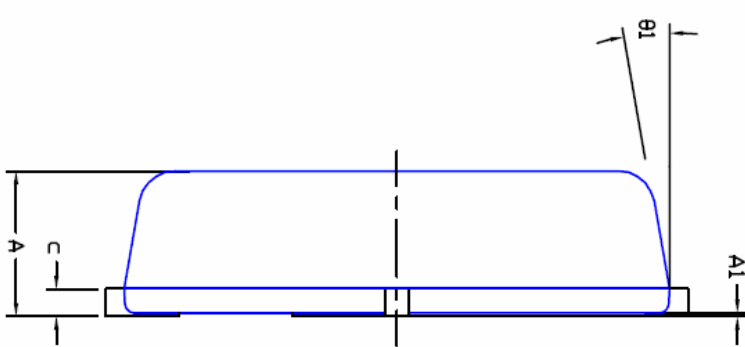
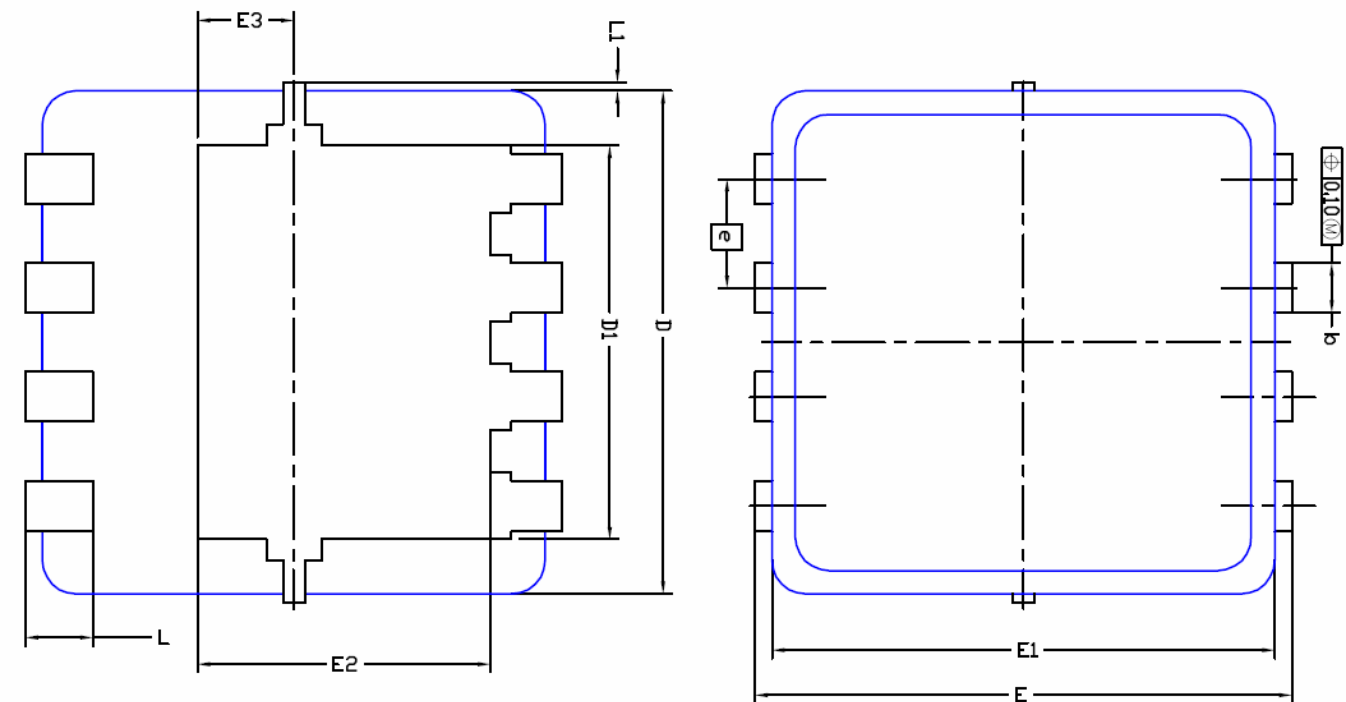


Figure 14 Normalized Maximum Transient Thermal Impedance

DFN3X3 EP Package Information



DIM.	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.80	0.900	0.0276	0.0315	0.0354
A1	0.00	---	0.05	0.000	---	0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.10	0.152	0.25	0.004	0.006	0.010
D	3.00 BSC			0.118 BSC		
D1	2.35 BSC			0.093 BSC		
E	3.20 BSC			0.126 BSC		
E1	3.00 BSC			0.118 BSC		
E2	1.75 BSC			0.069 BSC		
E3	0.575 BSC			0.023 BSC		
e	0.65 BSC			0.026 BSC		
L	0.30	0.40	0.50	0.0118	0.0157	0.0197
L1	0	---	0.100	0	---	0.004
θ1	0°	10°	12°	0°	10°	12°